



PROTON-ELECTROTEX RUSSIA

High power cycling capability
Low on-state and switching losses
Optimized for line frequency rectifiers
Designed for traction and industrial applications

Rectifier Diode Type D173-2500-44

Average forward current		I _{FAV}	2500 A	
Repetitive peak reverse voltage		V _{RRM}	3800...4400 V	
V _{RRM} , V	3800	4000	4200	4400
Voltage code	38	40	42	44
T _j , °C	-60...+150			

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I _{FAV}	Maximum allowable average forward current	A	2500 2919	T _c =110 °C; Double side cooled; T _c =100 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I _{FRMS}	RMS forward current	A	3925	T _c =110 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I _{FSM}	Surge forward current	kA	56.0 64.0	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V
			59.0 68.0	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V
I ² t	Safety factor	A ² s·10 ³	15600 20400	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V
			14400 19100	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V
BLOCKING					
V _{RRM}	Repetitive peak reverse voltages	V	3800...4400	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; 50 Hz	
V _{RSM}	Non-repetitive peak reverse voltages	V	3900...4500	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; single pulse	
V _R	Reverse continuous voltages	V	0.6·V _{RRM}	T _j =T _{j max} ;	
THERMAL					
T _{stg}	Storage temperature	°C	−60...+50		
T _j	Operating junction temperature	°C	−60...+150		
MECHANICAL					
F	Mounting force	kN	40...50		
a	Acceleration	m/s ²	50	Device clamped	

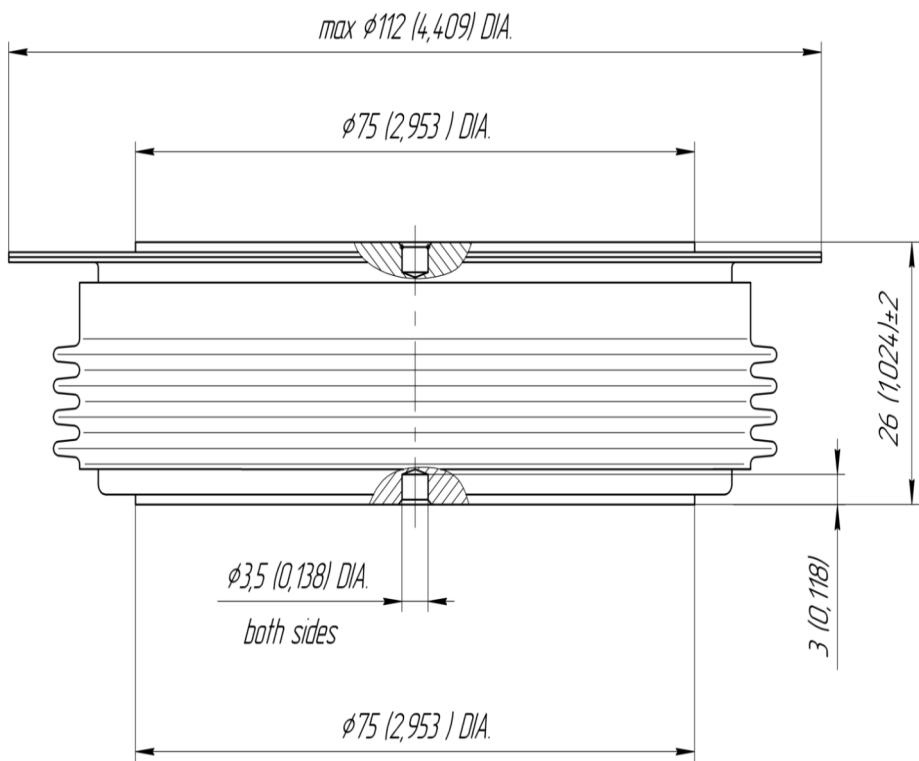
CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{FM}	Peak forward voltage, max	V	1.80	$T_j=25\text{ }^{\circ}\text{C}; I_{FM}=7850\text{ A}$	
$V_{F(TO)}$	Forward threshold voltage, max	V	1.092	$T_j=T_{j\text{ max}};$ $0.5\pi I_{FAV} < I_T < 1.5\pi I_{FAV}$	
r_T	Forward slope resistance, max	mΩ	0.129		
BLOCKING					
I_{RRM}	Repetitive peak reverse current, max	mA	150	$T_j=T_{j\text{ max}};$ $V_R=V_{RRM}$	
SWITCHING					
Q_r	Recovered charge, max	μC	11470	$T_j=T_{j\text{ max}};$ $I_{TM}=1000\text{ A};$ $di_R/dt=-5\text{ A}/\mu\text{s};$ $V_R=100\text{ V};$	
t_{rr}	Reverse recovery time, max	μS	124		
I_{rr}	Reverse recovery current, max	A	185		
THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.0085	Direct current	Double side cooled
R_{thjc-A}			0.0187		Anode side cooled
R_{thjc-K}			0.0153		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0020	Direct current	
MECHANICAL					
m	Weight, max	g	1160		
D_s	Surface creepage distance	mm (inch)	41.40 (1.630)		
D_a	Air strike distance	mm (inch)	23.10 (0.909)		

PART NUMBERING GUIDE

D	173	2500	44	N
1	2	3	4	5

1. D — Rectifier Diode
2. Design version
3. Average forward current, A
4. Voltage code
5. Ambient conditions: N – normal; T – tropical



All dimensions in millimeters (inches)

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In the interest of product improvement, Proton-Electrotex reserves the right to change data sheet without notice.

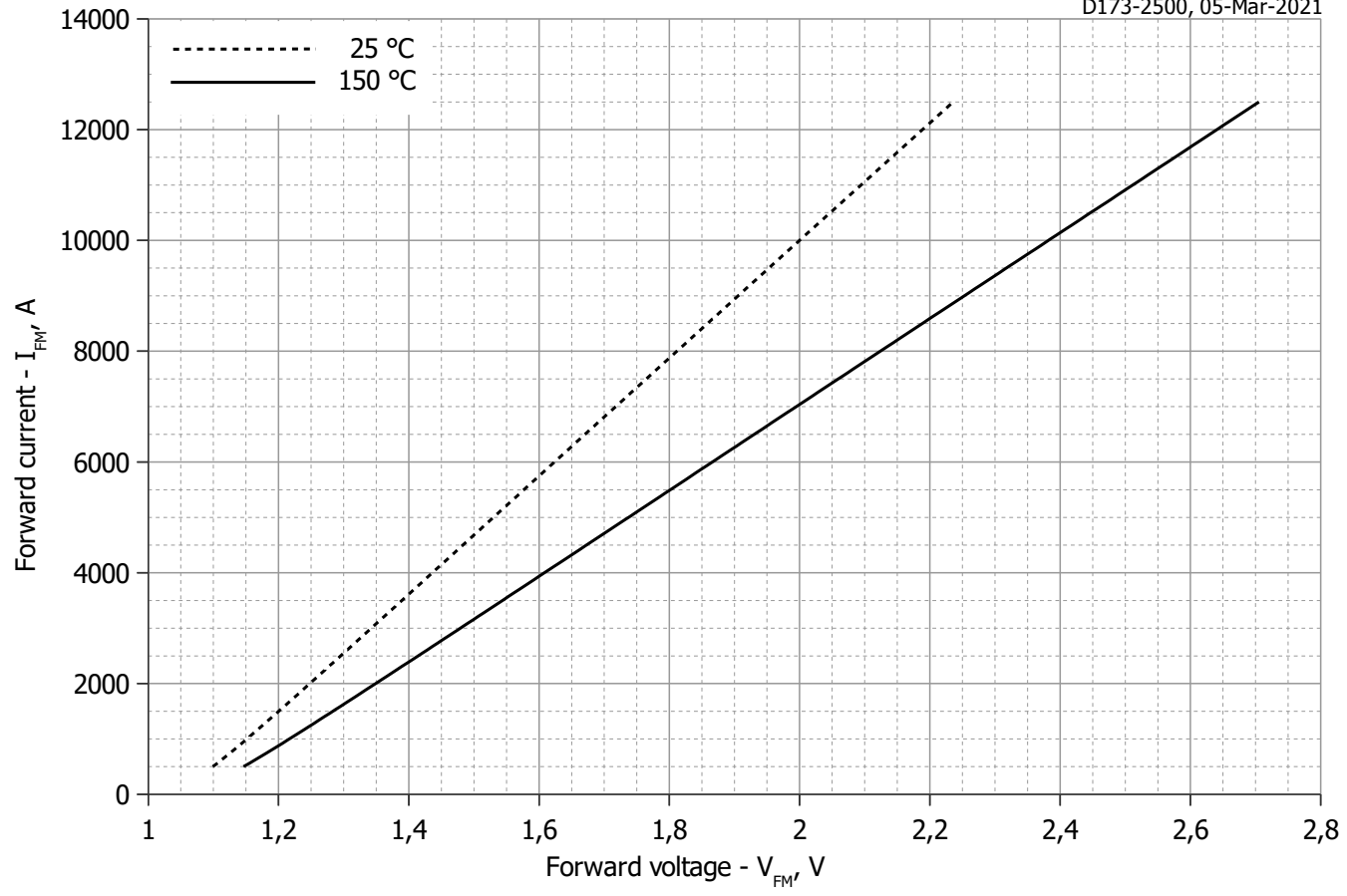


Fig 1 – Forward characteristics of Limit device

Analytical function for Forward characteristic:

$$V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Coefficients for max curves	
	$T_j = 25^{\circ}\text{C}$	$T_j = T_{j\text{ max}}$
A	0.94370586	0.97540394
B	0.00009864	0.00013263
C	0.02174767	0.02079742
D	-0.00130466	-0.00111077

Forward characteristic model (see Fig. 1).

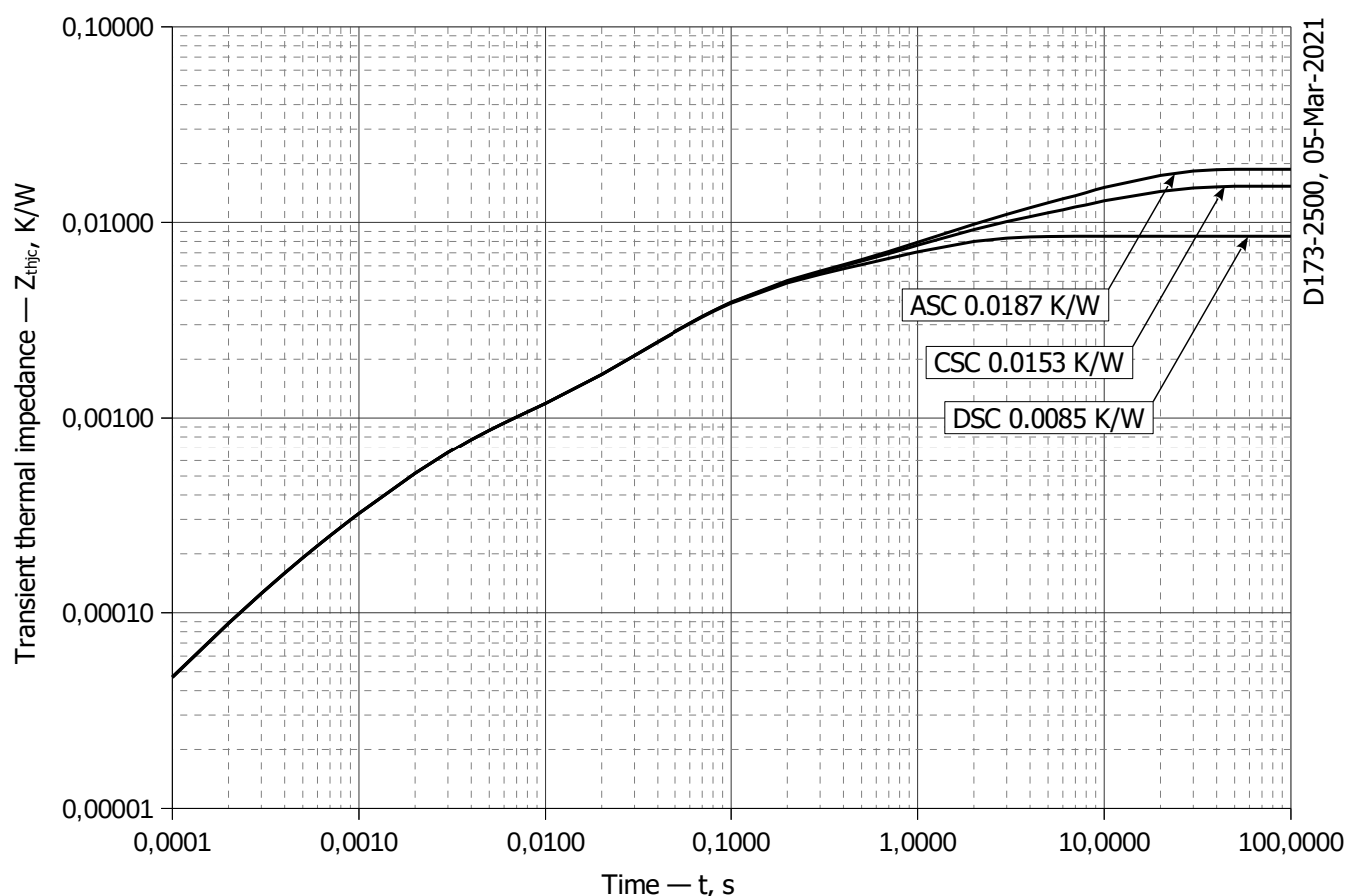


Fig 2 – Transient thermal impedance

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
R_i , K/W	0.00007989	0.002973	0.0005936	0.000846	0.00005975	0.003948
τ_i , s	1.688	0.06219	0.002329	0.138	0.0003243	0.9533

DC Cathode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.006819	0.004034	0.0008595	0.002956	0.0005965	0.00005689
τ_i , s	9.744	1.025	0.1394	0.06237	0.002318	0.0003037

DC Anode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.01023	0.004062	0.0009401	0.002853	0.0005963	0.00005641
τ_i , s	9.747	1.058	0.1304	0.06179	0.002313	0.0003013

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

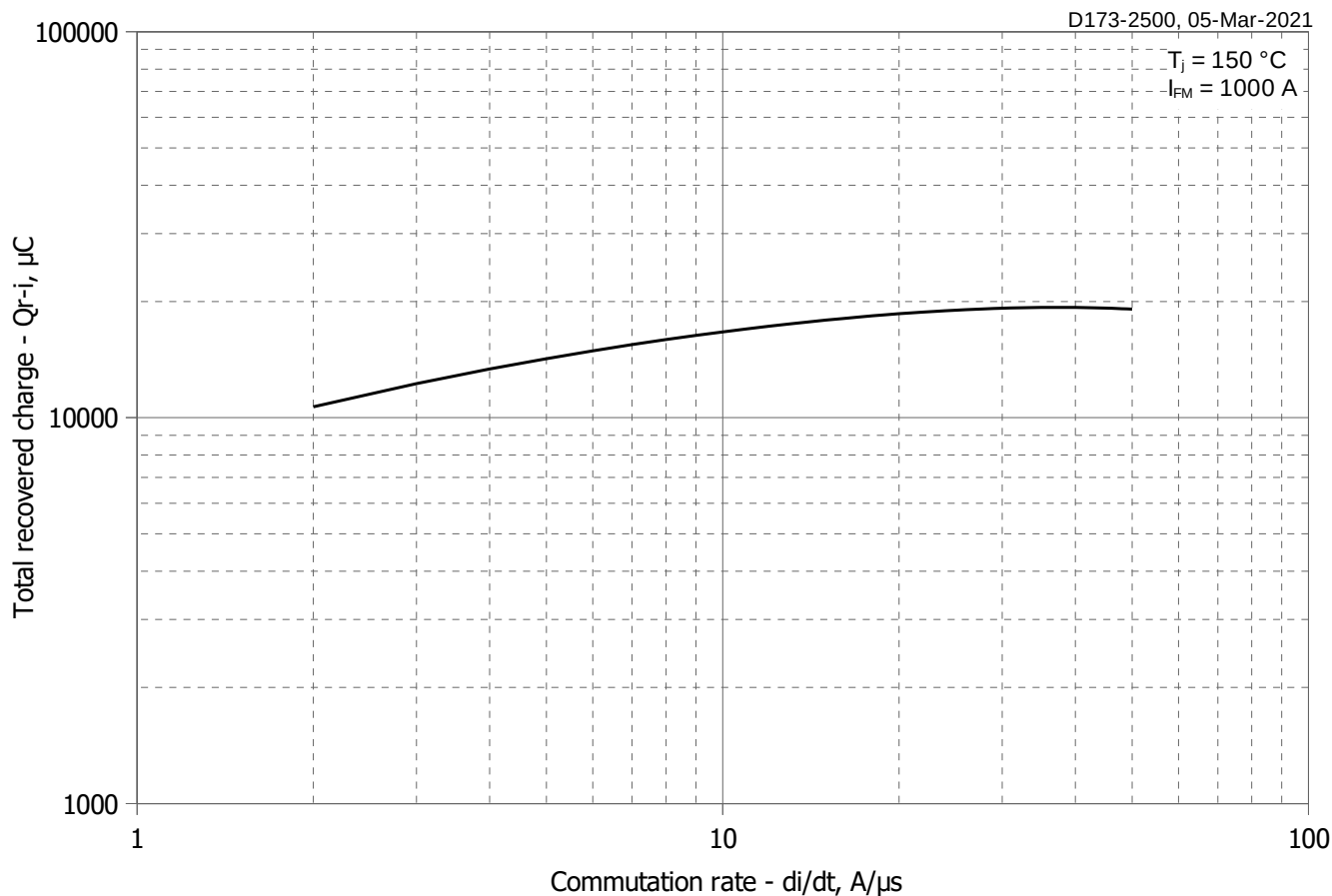


Fig 3 – Maximum recovered charge Q_{r-i} (integral) vs. commutation rate di_R/dt

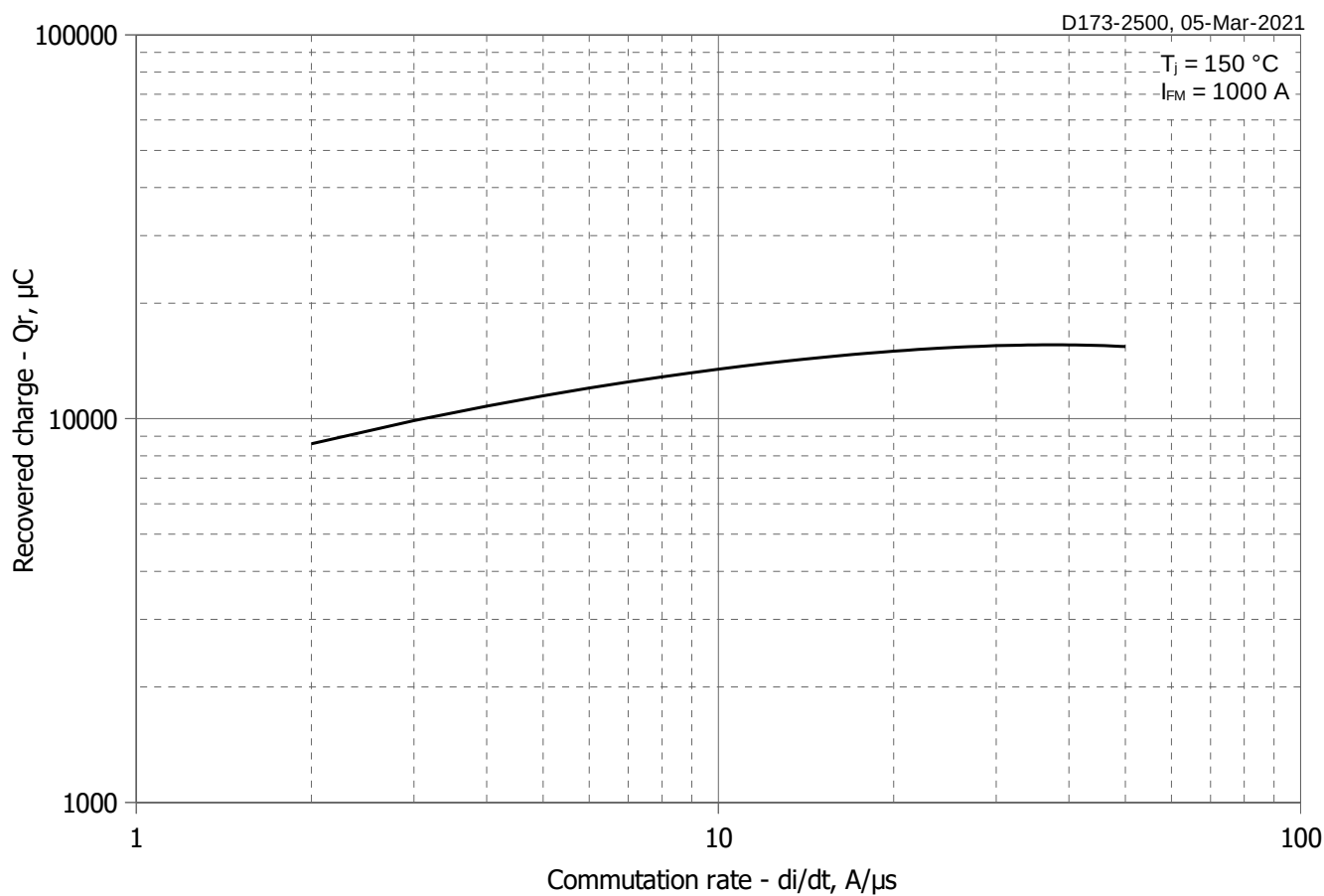


Fig 4 – Maximum recovered charge Q_r vs. commutation rate di_R/dt (25% chord)

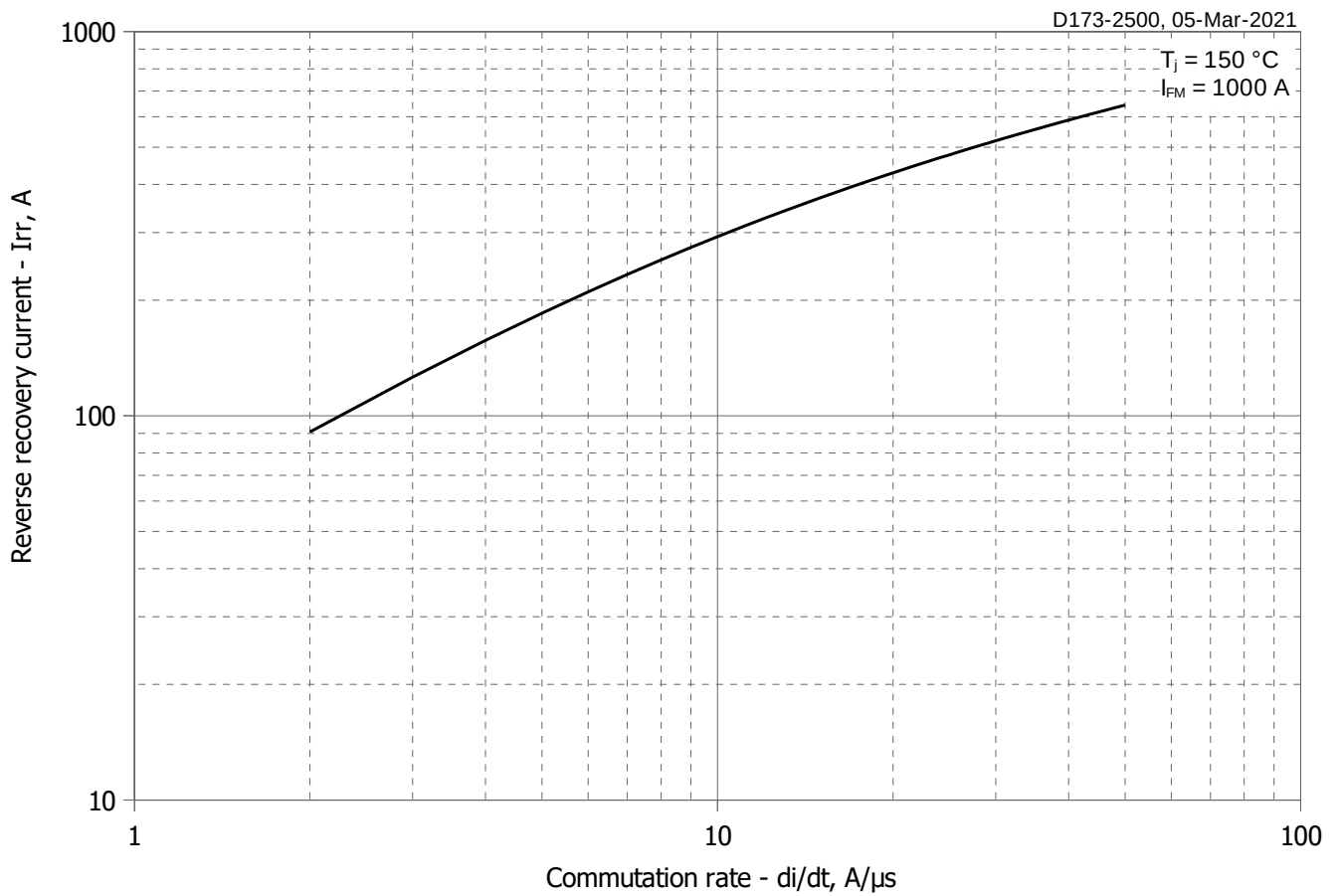


Fig 5 – Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

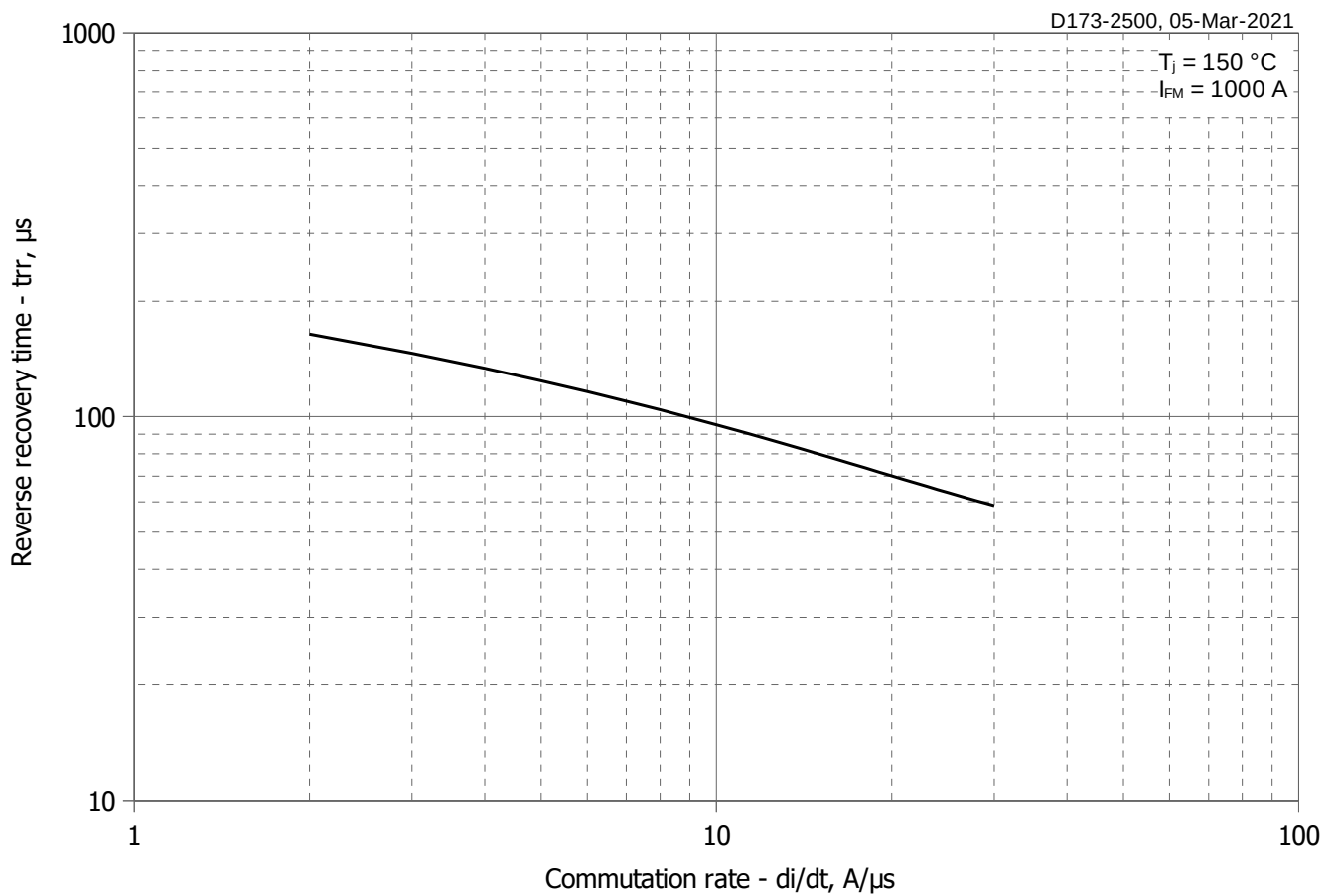


Fig 6 – Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)

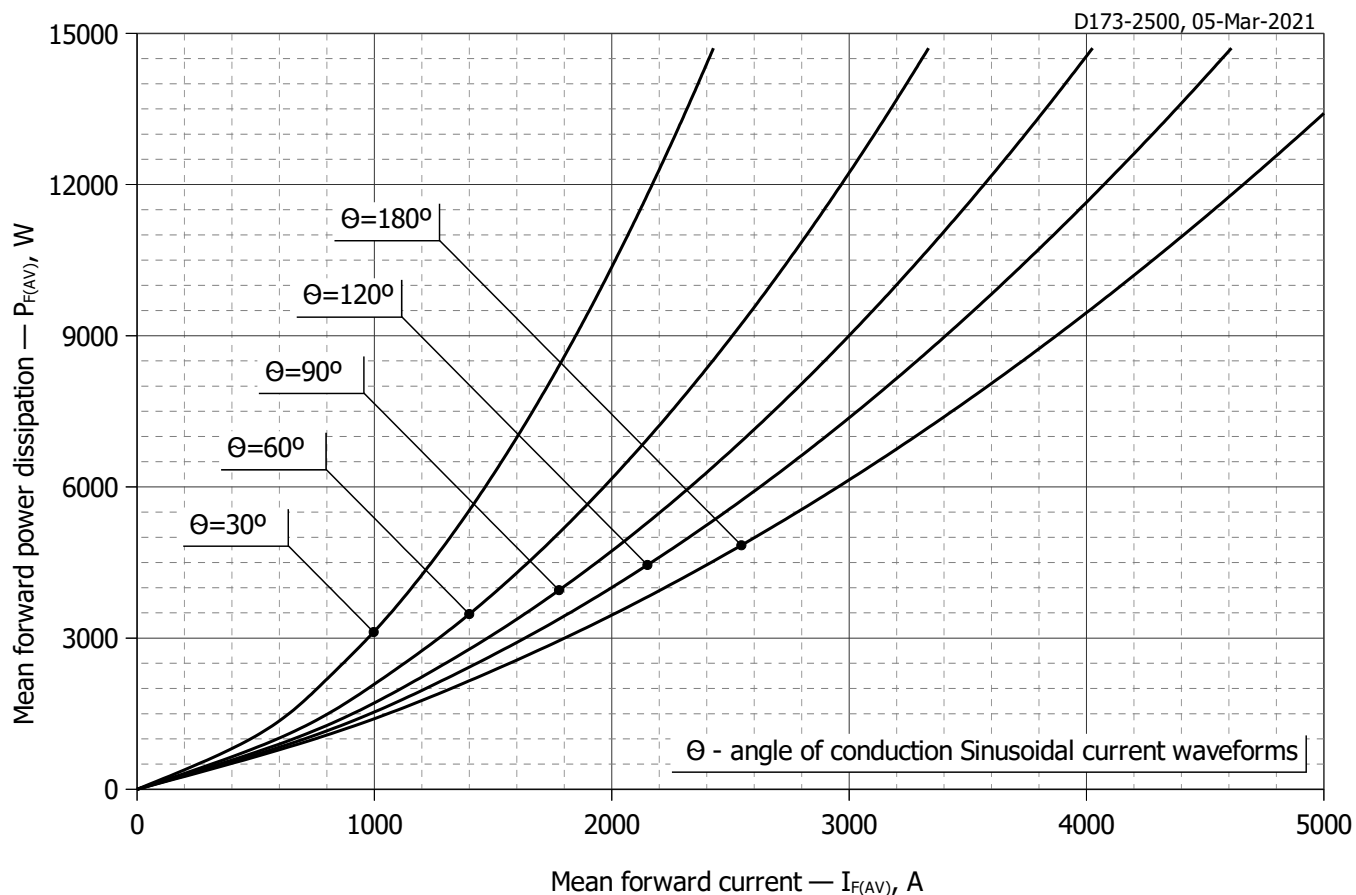


Fig. 7 - Mean forward power dissipation $P_{F(AV)}$ vs. mean forward current $I_{F(AV)}$ for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)

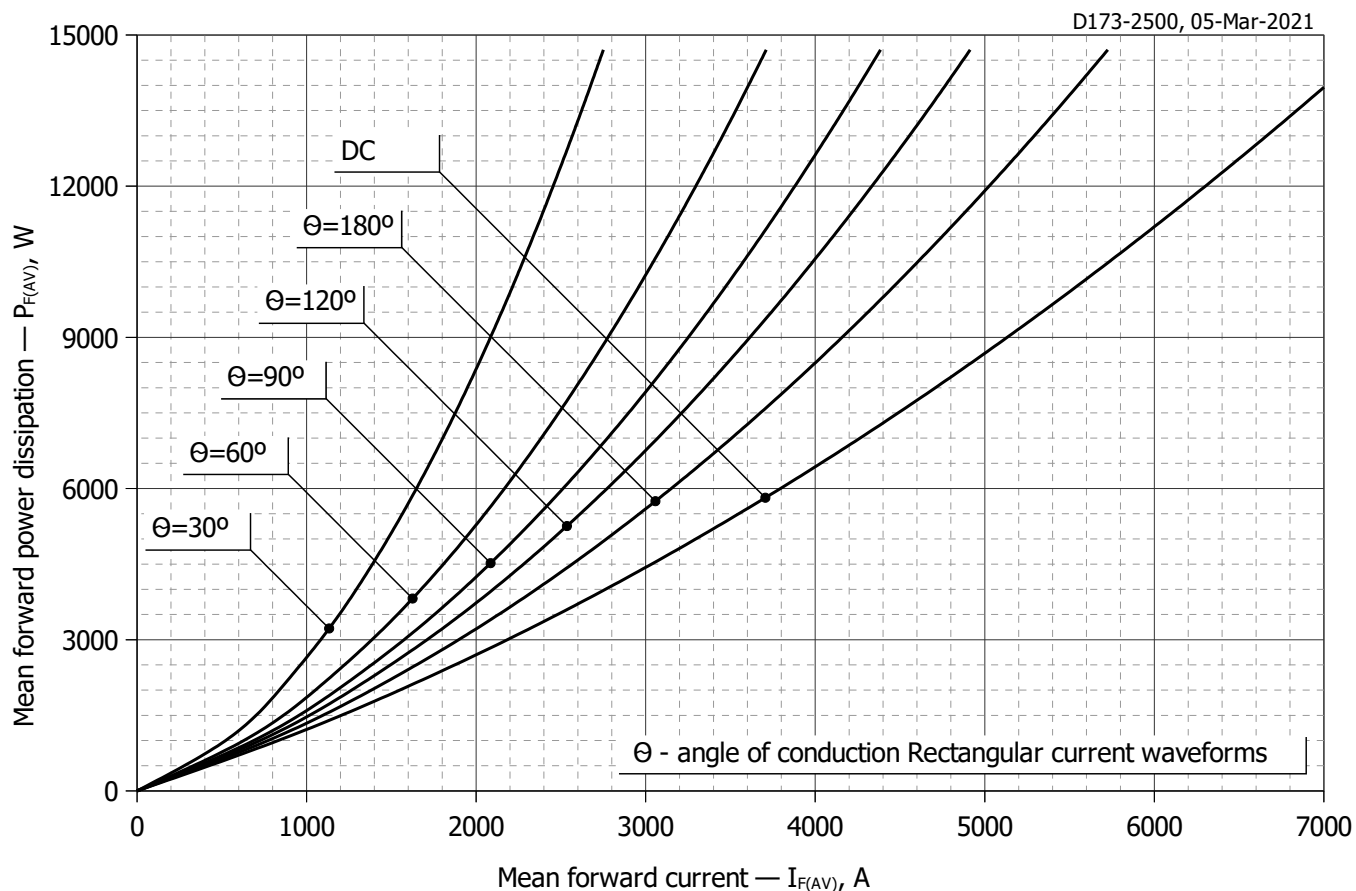


Fig. 8 – Mean forward power dissipation $P_{F(AV)}$ vs. mean forward current $I_{F(AV)}$ for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

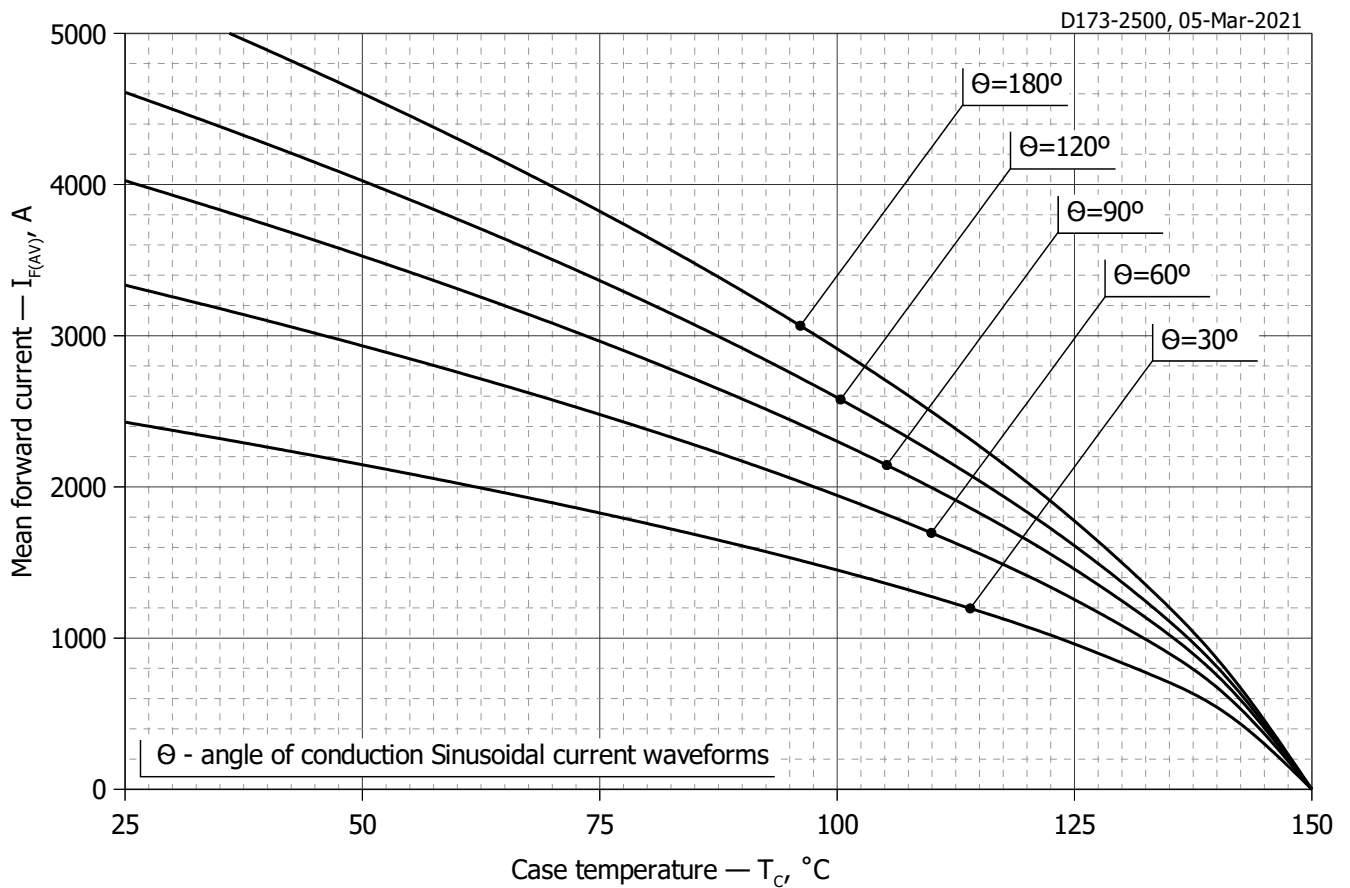


Fig. 9 – Mean forward current I_{FAV} vs. case temperature T_C for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)

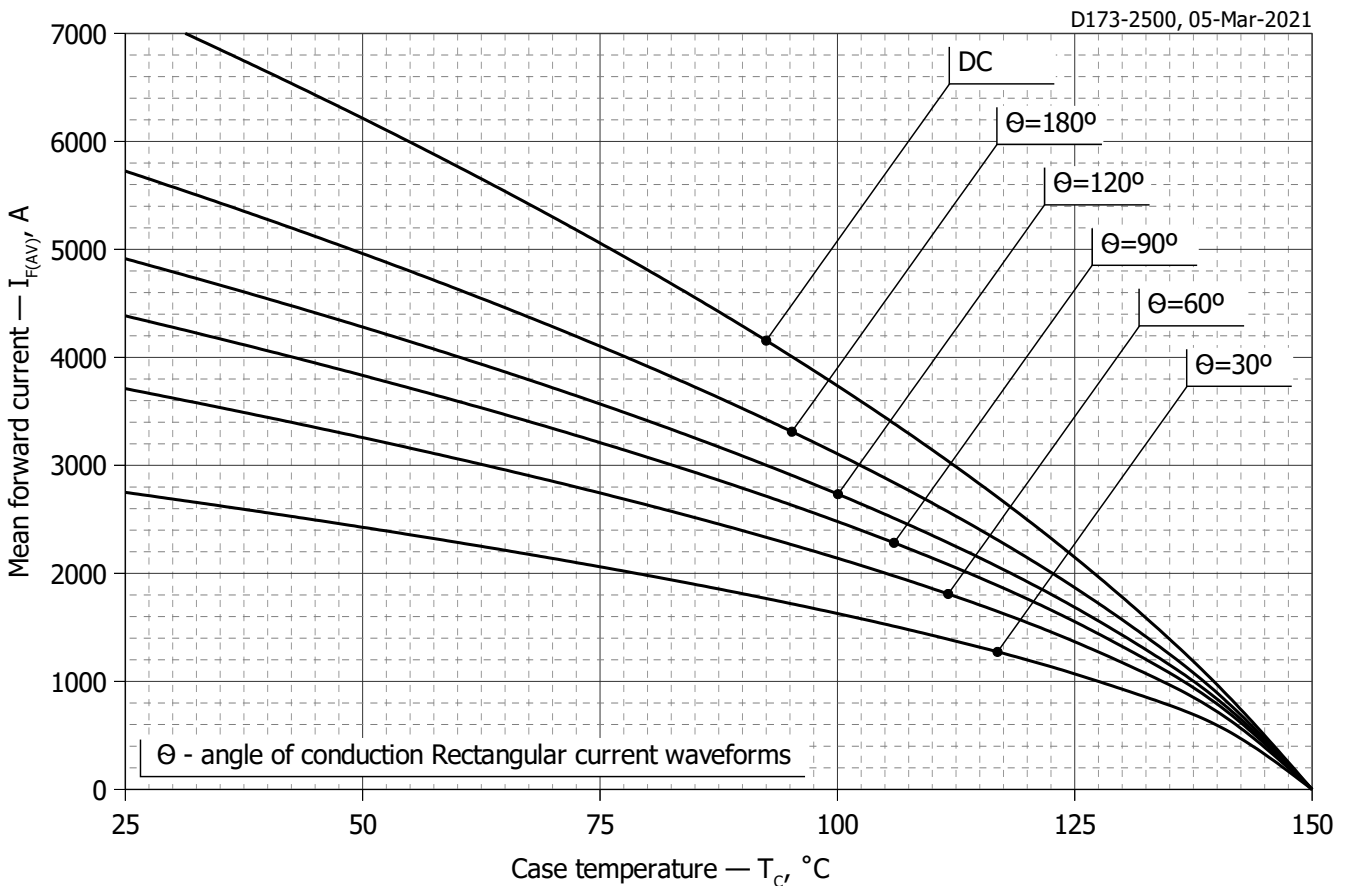


Fig. 10 - Mean forward current I_{FAV} vs. case temperature T_C for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

